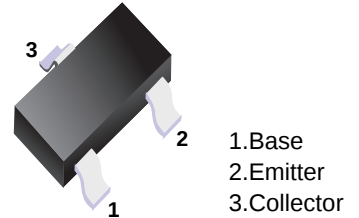


■ Simplified outline(SOT-323)

■ Features

- High Collector Current
- Complementary to SS8550W



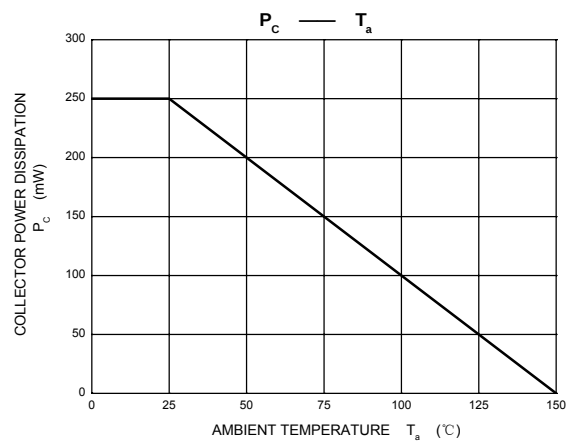
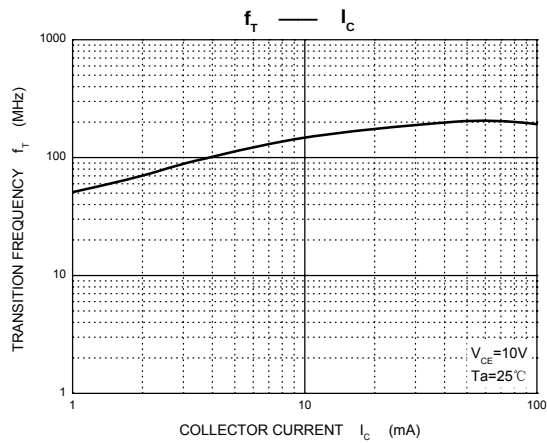
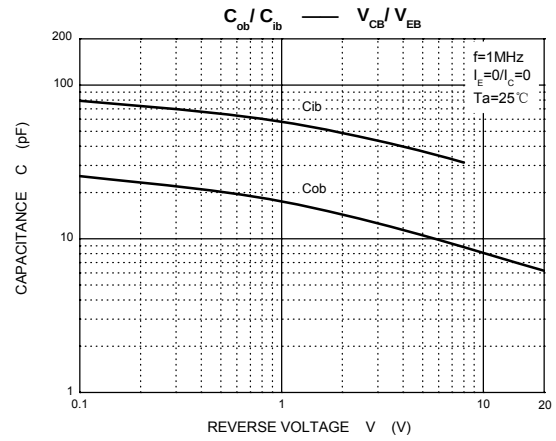
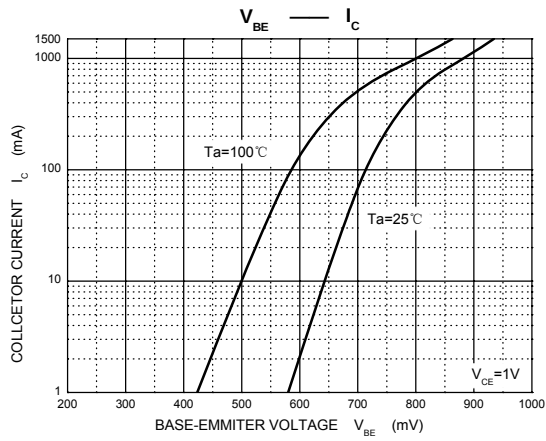
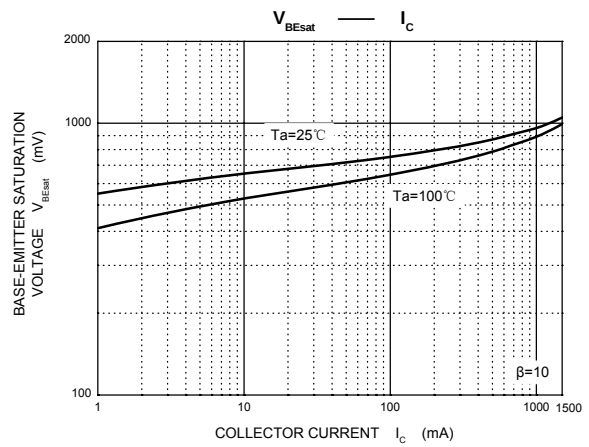
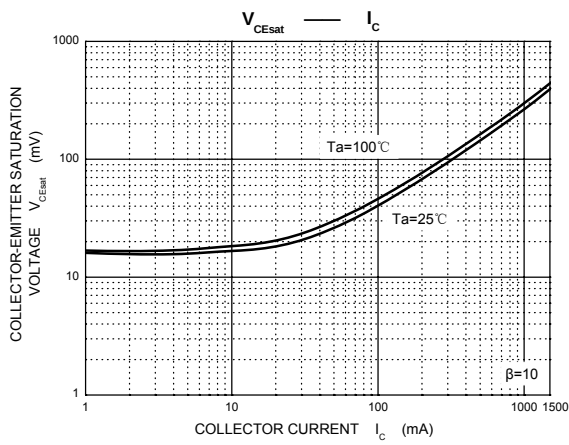
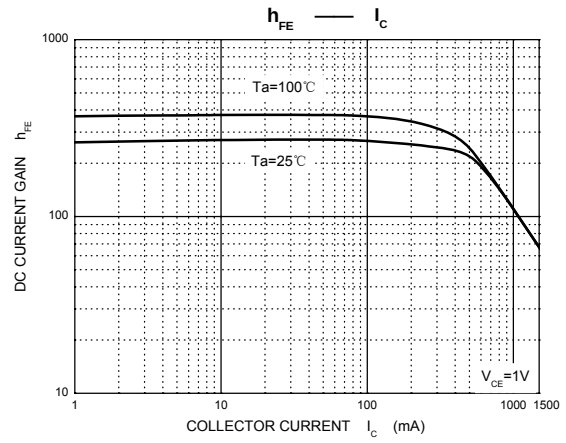
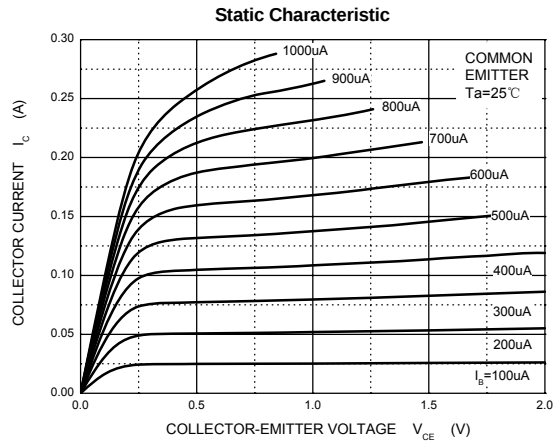
■ Absolute Maximum Ratings Ta = 25℃

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1.5	A
P_C	Collector Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

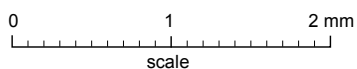
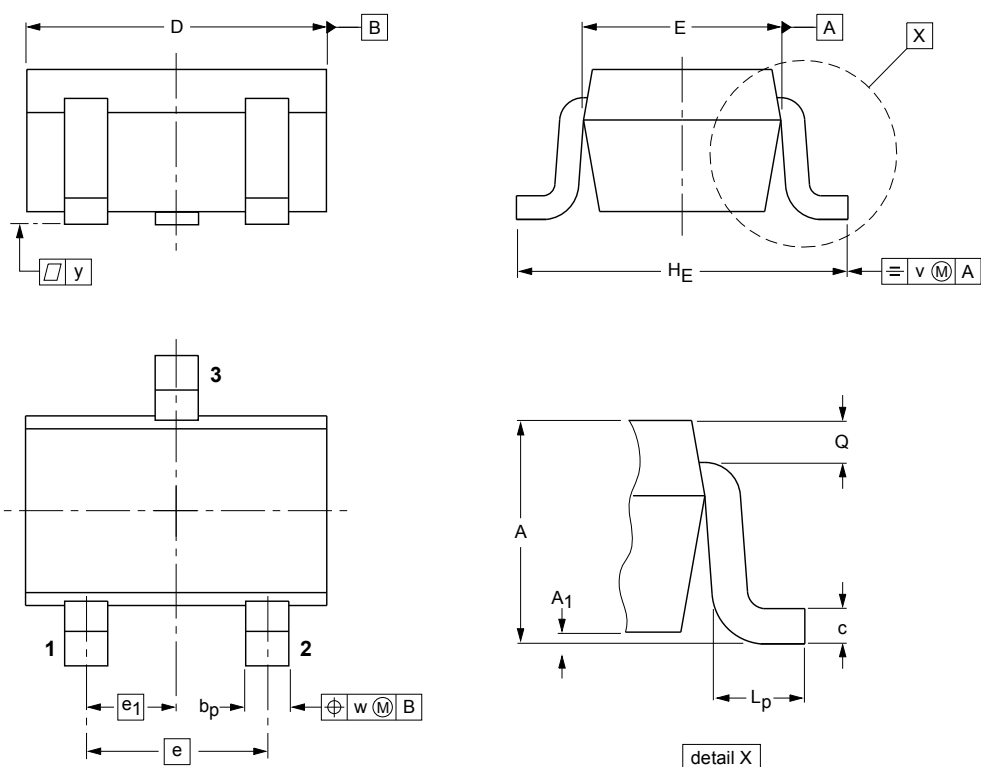
■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1mA, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 100mA$	120		400	
	$h_{FE(2)}$	$V_{CE} = 1V, I_C = 800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800mA, I_B = 80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800mA, I_B = 80mA$			1.2	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 50mA, f = 30MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			15	pF

RANK	SS8050W
RANGE	200 - 350
MARKING	Y1



■ SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2